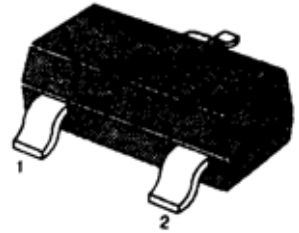


■■ APPLICATION: High current applications.

■■ MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

SOT-323

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	25	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	800	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}\text{C}$



1.Base 2.Emitter 3.Collector

■■ ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	100		630		$V_{CE}=1\text{V}, I_C=100\text{mA}$
Collector Cut-off Current	I_{CBO}			0.1	μA	$V_{CB}=30\text{V}, I_E=0$
Emitter Cut-off Current	I_{EBO}			0.1	μA	$V_{EB}=4\text{V}, I_C=0$
Collector-Base Breakdown Voltage	BV_{CBO}	30			V	$I_C=0.1\text{mA}, I_E=0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	25			V	$I_C=1\text{mA}, I_B=0$
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	$I_E=0.1\text{mA}, I_C=0$
Base-Emitter On Voltage	$V_{BE(ON)}$			1.2	V	$V_{CE}=1\text{V}, I_C=100\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.7	V	$I_C=500\text{mA}, I_B=50\text{mA}$
Gain bandwidth product	f_T	50	100		MHz	$I_C=10\text{mA}, V_{CE}=5\text{V}, f=50\text{MHz}$
Collector-Emitter Saturation Voltage	C_{ob}			12	pF	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$

■■ h_{FE} Classification And Marking

Print Mark	8GA	8GB	8GC
Classification	16	25	40
h_{FE}	100~250	160~400	250~630